INTERNATIONAL RECTIFIER IOR

HiRel Business Unit

PRODUCT / PROCESS CHANGE NOTIFICATION

To Be Completed By Change Initiator

DATE: December 2, 2013 | **NOTIFICATION REF:** NA | ☐ **APPROVAL** ☒ **NOTIFICATION**

PRODUCT / PROCESS REFERENCE: Wafer fabrication change for R5 and R7 Rad Hard P-Channel MOSFET products (see attached list)

TYPE OF CHANGE: ☒ **MAJOR** ☐ **MINOR** ☐ **EDITORIAL** | ☐ **PROCESS** ☒ **PRODUCT**

DETAILED DESCRIPTION OF CHANGE: (Include From / To condition and specific document(s) that are changing)

The following changes were made to the die construction:

1) The die design was changed from active area bonding to non-active area bonding. (ie. dedicated bond pad for source wire).
2) Minor changes to the fabrication process were also made using “best practice” approach.

DETAILED REASON FOR CHANGE:

International Rectifier wafer fab has made a process change for yield improvement with its p-channel stripe planar technology devices which include wire bonding over active area. Specifically, die design change was made to allow for non-active area bonding. These changes are in line with International Rectifiers R4 and R5 non-active area bond pad technology. Wafer Fab “Best- Practice” processes where applied during the design change to enhance product quality and repeatability.

Please note; all die change activity related to QPL products have been coordinated with DLA and are qualified in accordance with table E-III (Test guidelines for changes to qualified products) of MIL-PRF-19500.

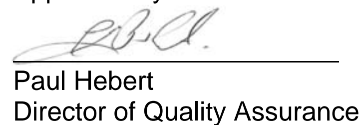
EFFECTIVITY DATE: See attached qualification plan and status

IMPACT OF CHANGE: No Impact to device performance

Change Initiator:

_*Kelley Price*__________________
Kelley Price
JAN Military Program Manager

Approved By:



Paul Hebert
Director of Quality Assurance

QPL Part Number	Q P L Part Desriptions						IR Generic Part Number	PLATFORM Qualification Status
	Die Information				QPL Slash	Device Package		
	Gen.	Size	Voltage	Type				
2N7519U3	R5	3	30V	P-ch	/ 732	SMD-0.5	IRHNJ597Z30	Qualified die available, no shipment delays - Implementing dedicated non-active bond pad planned
2N7519T3	R5	3	30V	P-ch	/ 732	TO-257AA	IRHYS597Z30CM	
2N7523U2	R5	6	30V	P-ch	/ 733	SMD-2	IRHNA597Z60	
2N7523T1	R5	6	30V	P-ch	/ 733	TO-254AA	IRHMS597Z60	
2N7520U3	R5	3	60V	P-ch	/ 732	SMD-0.5	IRHNJ597034	Qualified die available, no shipment delays - Implementing dedicated non-active bond pad planned
2N7520T3	R5	3	60V	P-ch	/ 732	TO-257AA	IRHYS597034CM	
2N7524U2	R5	6	60V	P-ch	/ 733	SMD-2	IRHNA597Z60	
2N7524T1	R5	6	60V	P-ch	/ 733	TO-254AA	IRHMS597064	April 2014
2N7624U3	R7	3	60V	P-ch	not QPL'ed	SMD-0.5	IRHLNJ797034	Implementing dedicated non-active area bond pad Spring 2014
2N7622U2	R7	6	60V	P-ch	not QPL'ed	SMD-2	IRHLNA797064	
2N7623T1	R7	6	60V	P-ch	not QPL'ed	TO-254	IRHLMS797064	
2N7625T3	R7	3	60V	P-ch	not QPL'ed	TO-257AA	IRHLYS797034	
2N7626UB	R7	Z	60V	P-ch	/745	UB	IRHLUB7970Z4	December 2013
2N7627UC	R7	Z	60V	P-ch	/745	UC	IRHLUC7970Z4	
2N7628M1	R7	Z	60V	P-ch	not QPL'ed	MO-36AB	IRHLG7970Z4	
2N7629U6	R7	Z	60V	P-ch	not QPL'ed	LCC-28	IRHLQ7970Z4	
2N7631T2	R7	Z	60V	P-ch	not QPL'ed	TO-39	IRHLF7970Z4	